

October 2008

KSC5021 NPN Silicon Transistor

- · High Voltage and High Reliability
- High Speed Switching : $t_F = 0.1 \mu s$ (Typ.)
- · Wide SOA



1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	500	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	5	А
I _{CP}	Collector Current (Pulse)	10	А
I _B	Base Current	2	А
P _C	Collector Dissipation (T _C =25°C)	50	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1mA, I _E = 0	800			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA, I _B = 0	500			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA, I _C = 0	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	I _C = 2.5A, I _{B1} = -I _{B2} = 1A L = 1mH, Clamped	500			V
I _{CBO}	Collector Cut-off Current	V _{CB} = 500V, I _E = 0			10	μА
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5V, I _C = 0			10	μА
h _{FE1}	DC Current Gain	V _{CE} = 5V, I _C = 0.6A V _{CE} = 5V, I _C = 3A	15 8		50	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 3A, I _B = 0.6A			1	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 3A, I _B = 0.6A			1.5	V
C _{ob}	Output Capacitance	V _{CB} = 10V, I _E = 0, f=1MHz		80		pF
f _T	Current Gain Bandwidth Product	V _{CE} = 10V, I _C = 0.6A		18		MHz
t _{ON}	Turn On Time	V _{CC} = 200V			0.5	μS
t _{STG}	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 4A$ $R_1 = 50\Omega$			3	μS
t _F	Fall Time				0.3	μS

^{*} Pulse Test: PW $\leq 300 \mu s, \, \text{Duty Cycle} \leq 2\%$

h_{FE} Classification

Classification	R	0	Y
h _{FE1}	15 ~ 30	20 ~ 40	30 ~ 50

Typical Performance Characteristics

Figure 1. Static Characteristic

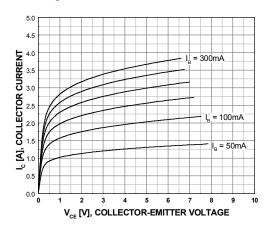


Figure 3. DC Current Gain (O-Grade)

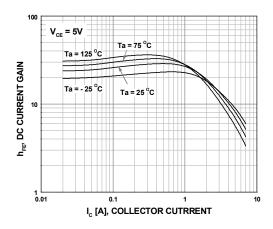


Figure 5. Saturatin Voltage (O-Grade)

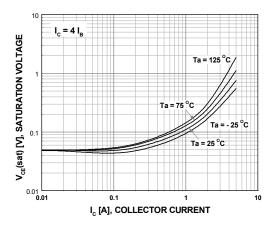


Figure 2. DC Current Gain (R-Grade)

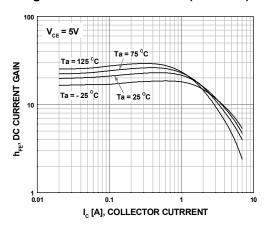


Figure 4. Saturation Voltage (R-Grade)

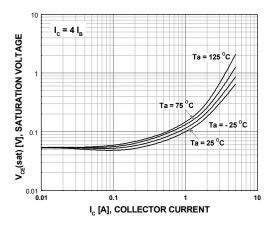
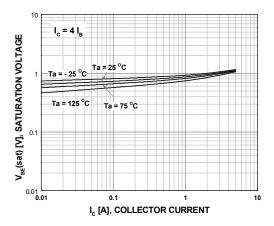


Figure 6. Saturation Voltage (R-Grade)



Typical Characteristics

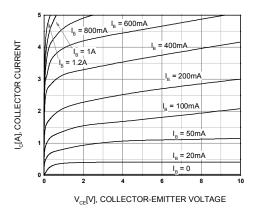
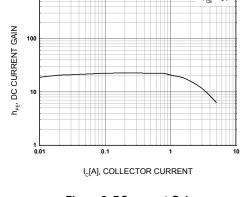


Figure 1. Static Characteristic



1000

Figure 2. DC current Gain

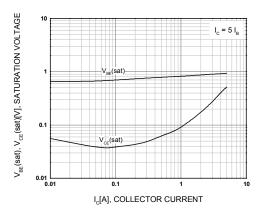


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

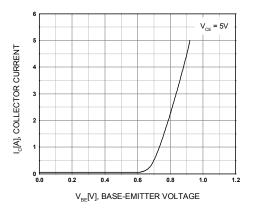


Figure 4. Base-Emitter On Voltage

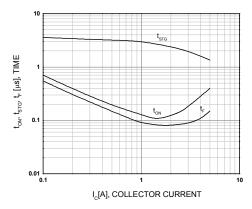


Figure 5. Switching Time

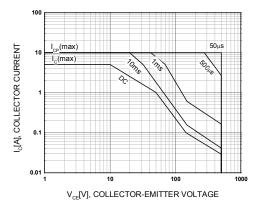


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

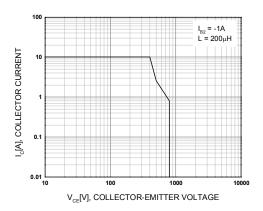


Figure 7. Reverse Bias Safe Operating Area

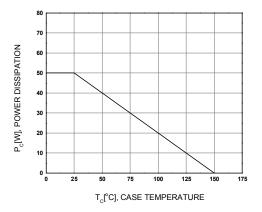
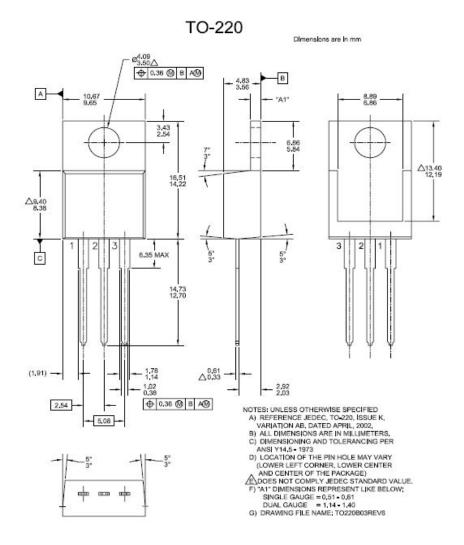


Figure 8. Power Derating

Package Dimension







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